

La nouvelle puce 3D d'IBM va doper les smartphones et les PC

15 fois plus rapide et 90% plus petite

Paris - 02 déc. 2011: IBM et Micron annoncent le lancement d'une puce 3D dotée d'une mémoire 15 fois plus rapide, utilisant moins d'énergie et d'espace.

Micron sera le premier à utiliser ce procédé IBM pour offrir un nouveau type de mémoire avancée – l'*Hybrid Memory Cube* 3D (HMC) destiné aux smartphones et PC. Mis sur le marché dès l'an prochain, il promet une performance 15 fois supérieur dans un package réduit de 90%.

L'HMC offre une bande passante et une efficacité largement supérieures aux capacités des dispositifs actuels. Les prototypes HMC, par exemple, offrent un débit de 128 gigaoctets par seconde (Go/s). Pour comparaison, les dispositifs actuels de pointe plafonnent à un débit de 12,8 Go/s.

IBM to Produce Micron's Hybrid Memory Cube in debut of First Commercial, 3D Chip-Making Capability

New process creates 15-times-faster memory in 90% smaller package

ARMONK, N.Y. and BOISE, Idaho, December 1, 2011 - IBM (NYSE: IBM) and Micron Technology, Inc., announced today that Micron will begin production of a new memory device built using the first commercial CMOS manufacturing technology to employ through-silicon vias (TSVs). IBM's advanced TSV chip-making process enables Micron's Hybrid Memory Cube (HMC) to achieve speeds 15 times faster than today's technology.

IBM will present the details of its TSV manufacturing breakthrough at the IEEE International Electron Devices Meeting on December 5 in Washington, DC.

HMC parts will be manufactured at IBM's advanced semiconductor fab in East Fishkill, N.Y., using the company's 32nm, high-K metal gate process technology.

HMC technology uses advanced TSVs — vertical conduits that electrically connect a stack of individual chips — to combine high-performance logic with Micron's state-of-the-art DRAM. HMC delivers bandwidth and

efficiencies a leap beyond current device capabilities. HMC prototypes, for example, clock in with bandwidth of 128 gigabytes per second (GB/s). By comparison, current state-of-the-art devices deliver 12.8 GB/s. HMC also requires 70 percent less energy to transfer data while offering a small form factor— just 10 percent of the footprint of conventional memory.

HMC will enable a new generation of performance in applications ranging from large-scale networking and high-performance computing, to industrial automation and, eventually, consumer products.

“Our ability to use TSVs in commercial CMOS production and integrating other chip technology, such as high-speed communications, is a key advancement in the move to 3D semiconductor manufacturing,” said Subu Iyer, IBM Fellow. “The TSV manufacturing process that we will describe in December will have applications beyond memory, enabling other industry segments as well.”

“HMC is a game changer, finally giving architects a flexible memory solution that scales bandwidth while addressing power efficiency,” said Scott Graham, General Manager of DRAM Solutions for Micron. “Through collaboration with IBM, Micron will provide the industry’s most capable memory offering.”

Additional information, technical specifications, tools and support for adopting HMC technology can be found at micron.com.

About Micron

Micron Technology, Inc, is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets a full range of DRAM, NAND and NOR flash memory, as well as other innovative memory technologies, packaging solutions and semiconductor systems for use in leading-edge computing, consumer, networking, embedded and mobile products. Micron’s common stock is traded on the NASDAQ under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

About IBM

For more information about IBM's advanced semiconductor products and manufacturing processes visit www.ibm.com/chips
